NXP USA Inc. - KMPC8313ECVRAFFB Datasheet





Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of **Embedded - Microprocessors**

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details

Product Status	Obsolete
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	333MHz
Co-Processors/DSP	Security; SEC 2.2
RAM Controllers	DDR, DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100/1000Mbps (2)
SATA	-
USB	USB 2.0 + PHY (1)
Voltage - I/O	1.8V, 2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	Cryptography
Package / Case	516-BBGA Exposed Pad
Supplier Device Package	516-TEPBGA (27x27)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/kmpc8313ecvraffb

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



1 Overview

The MPC8313E incorporates the e300c3 core, which includes 16 Kbytes of L1 instruction and data caches and on-chip memory management units (MMUs). The MPC8313E has interfaces to dual enhanced three-speed 10/100/1000 Mbps Ethernet controllers, a DDR1/DDR2 SDRAM memory controller, an enhanced local bus controller, a 32-bit PCI controller, a dedicated security engine, a USB 2.0 dual-role controller and an on-chip high-speed PHY, a programmable interrupt controller, dual I²C controllers, a 4-channel DMA controller, and a general-purpose I/O port. This figure shows a block diagram of the MPC8313E.



Figure 1. MPC8313E Block Diagram

The MPC8313E security engine (SEC 2.2) allows CPU-intensive cryptographic operations to be offloaded from the main CPU core. The security-processing accelerator provides hardware acceleration for the DES, 3DES, AES, SHA-1, and MD-5 algorithms.

1.1 MPC8313E Features

The following features are supported in the MPC8313E:

- Embedded PowerPCTM e300 processor core built on Power ArchitectureTM technology; operates at up to 333 MHz.
- High-performance, low-power, and cost-effective host processor
- DDR1/DDR2 memory controller—one 16-/32-bit interface at up to 333 MHz supporting both DDR1 and DDR2
- 16-Kbyte instruction cache and 16-Kbyte data cache, a floating point unit, and two integer units
- Peripheral interfaces such as 32-bit PCI interface with up to 66-MHz operation, 16-bit enhanced local bus interface with up to 66-MHz operation, and USB 2.0 (high speed) with an on-chip PHY.
- Security engine provides acceleration for control and data plane security protocols
- Power management controller for low-power consumption
- High degree of software compatibility with previous-generation PowerQUICC processor-based designs for backward compatibility and easier software migration



1.6 USB Dual-Role Controller

The MPC8313E USB controller includes the following features:

- Supports USB on-the-go mode, which includes both device and host functionality, when using an external ULPI (UTMI + low-pin interface) PHY
- Compatible with Universal Serial Bus Specification, Rev. 2.0
- Supports operation as a stand-alone USB device
 - Supports one upstream facing port
 - Supports three programmable USB endpoints
- Supports operation as a stand-alone USB host controller
 - Supports USB root hub with one downstream-facing port
 - Enhanced host controller interface (EHCI) compatible
- Supports high-speed (480 Mbps), full-speed (12 Mbps), and low-speed (1.5 Mbps) operation. Low-speed operation is supported only in host mode.
- Supports UTMI + low pin interface (ULPI) or on-chip USB 2.0 full-speed/high-speed PHY

1.7 Dual Enhanced Three-Speed Ethernet Controllers (eTSECs)

The MPC8313E eTSECs include the following features:

- Two RGMII/SGMII/MII/RMII/RTBI interfaces
- Two controllers designed to comply with IEEE Std 802.3®, 802.3u®, 802.3x®, 802.3z®, 802.3au®, and 802.3ab®
- Support for Wake-on-Magic Packet[™], a method to bring the device from standby to full operating mode
- MII management interface for external PHY control and status
- Three-speed support (10/100/1000 Mbps)
- On-chip high-speed serial interface to external SGMII PHY interface
- Support for IEEE Std 1588TM
- Support for two full-duplex FIFO interface modes
- Multiple PHY interface configuration
- TCP/IP acceleration and QoS features available
- IP v4 and IP v6 header recognition on receive
- IP v4 header checksum verification and generation
- TCP and UDP checksum verification and generation
- Per-packet configurable acceleration
- Recognition of VLAN, stacked (queue in queue) VLAN, IEEE Std 802.2[®], PPPoE session, MPLS stacks, and ESP/AH IP-security headers
- Transmission from up to eight physical queues.
- Reception to up to eight physical queues



1.10 Serial Peripheral Interface (SPI)

The serial peripheral interface (SPI) allows the MPC8313E to exchange data between other PowerQUICC family chips, Ethernet PHYs for configuration, and peripheral devices such as EEPROMs, real-time clocks, A/D converters, and ISDN devices.

The SPI is a full-duplex, synchronous, character-oriented channel that supports a four-wire interface (receive, transmit, clock, and slave select). The SPI block consists of transmitter and receiver sections, an independent baud-rate generator, and a control unit.

1.11 DMA Controller, Dual I²C, DUART, Local Bus Controller, and Timers

The MPC8313E provides an integrated four-channel DMA controller with the following features:

- Allows chaining (both extended and direct) through local memory-mapped chain descriptors (accessible by local masters)
- Supports misaligned transfers

There are two I²C controllers. These synchronous, multi-master buses can be connected to additional devices for expansion and system development.

The DUART supports full-duplex operation and is compatible with the PC16450 and PC16550 programming models. The 16-byte FIFOs are supported for both the transmitter and the receiver.

The MPC8313E local bus controller (LBC) port allows connections with a wide variety of external DSPs and ASICs. Three separate state machines share the same external pins and can be programmed separately to access different types of devices. The general-purpose chip select machine (GPCM) controls accesses to asynchronous devices using a simple handshake protocol. The three user programmable machines (UPMs) can be programmed to interface to synchronous devices or custom ASIC interfaces. Each chip select can be configured so that the associated chip interface can be controlled by the GPCM or UPM controller. The FCM provides a glueless interface to parallel-bus NAND Flash E2PROM devices. The FCM contains three basic configuration register groups—BR*n*, OR*n*, and FMR. Both may exist in the same system. The local bus can operate at up to 66 MHz.

The MPC8313E system timers include the following features: periodic interrupt timer, real time clock, software watchdog timer, and two general-purpose timer blocks.

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8313E. The MPC8313E is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.



Characteristic	Symbol	Recommended Value ¹	Unit	Current Requirement
Core supply voltage	V _{DD}	1.0 V ± 50 mV	V	469 mA
Internal core logic constant power	V _{DDC}	1.0 V ± 50 mV	V	377 mA
SerDes internal digital power	XCOREV _{DD}	1.0	V	170 mA
SerDes internal digital ground	XCOREV _{SS}	0.0	V	—
SerDes I/O digital power	XPADV _{DD}	1.0	V	10 mA
SerDes I/O digital ground	XPADV _{SS}	0.0	V	_
SerDes analog power for PLL	SDAV _{DD}	1.0 V ± 50 mV	V	10 mA
SerDes analog ground for PLL	SDAV _{SS}	0.0	V	—
Dedicated 3.3 V analog power for USB PLL	USB_PLL_PWR3	3.3 V ± 300 mV	V	2–3 mA
Dedicated 1.0 V analog power for USB PLL	USB_PLL_PWR1	1.0 V ± 50 mV	V	2–3 mA
Dedicated analog ground for USB PLL	USB_PLL_GND	0.0	V	—
Dedicated USB power for USB bias circuit	USB_VDDA_BIAS	3.3 V ± 300 mV	V	4–5 mA
Dedicated USB ground for USB bias circuit	USB_VSSA_BIAS	0.0	V	—
Dedicated power for USB transceiver	USB_VDDA	3.3 V ± 300 mV	V	75 mA
Dedicated ground for USB transceiver	USB_VSSA	0.0	V	
Analog power for e300 core APLL	AV _{DD1} ⁶	1.0 V ± 50 mV	V	2–3 mA
Analog power for system APLL	AV _{DD2} ⁶	1.0 V ± 50 mV	V	2–3 mA
DDR1 DRAM I/O voltage (333 MHz, 32-bit operation)	GV _{DD}	2.5 V ± 125 mV	V	131 mA
DDR2 DRAM I/O voltage (333 MHz, 32-bit operation)	GV _{DD}	1.8 V ± 80 mV	V	140 mA
Differential reference voltage for DDR controller	MV _{REF}	$\begin{array}{c} \mbox{1/2 DDR supply} \\ \mbox{(0.49 \times GV_{DD} to} \\ \mbox{0.51 \times GV_{DD})} \end{array}$	V	_
Standard I/O voltage	NV _{DD}	$3.3 \text{ V} \pm 300 \text{ mV}^2$	V	74 mA
eTSEC2 I/O supply	LV _{DDA} 3.3 V ± 300 mV		V	22 mA
eTSEC1/USB DR I/O supply	LV _{DDB}	2.5 V ± 125 mV/ 3.3 V ± 300 mV	V	44 mA
Supply for eLBC IOs	LV _{DD}	3.3 V ± 300 mV	V	16 mA
Analog and digital ground	V _{SS}	0.0	V	_
Junction temperature range	T _A /T _J ³	0 to 105	°C	

Table 2. Recommended Operating Conditions



3 Power Characteristics

The estimated typical power dissipation, not including I/O supply power, for this family of MPC8313E devices is shown in this table. Table 5 shows the estimated typical I/O power dissipation.

Core Frequency (MHz)	CSB Frequency (MHz)	Typical ²	Maximum for Rev. 1.0 Silicon ³	Maximum for Rev. 2.x or Later Silicon ³	Unit
333	167	820	1020	1200	mW
400	133	820	1020	1200	mW

Table 4. MPC8313E Power Dissipation¹

Note:

 The values do not include I/O supply power or AV_{DD}, but do include core, USB PLL, and a portion of SerDes digital power (not including XCOREV_{DD}, XPADV_{DD}, or SDAV_{DD}, which all have dedicated power supplies for the SerDes PHY).

2. Typical power is based on a voltage of V_{DD} = 1.05 V and an artificial smoker test running at room temperature.

3. Maximum power is based on a voltage of V_{DD} = 1.05 V, a junction temperature of T_J = 105°C, and an artificial smoker test.

This table describes a typical scenario where blocks with the stated percentage of utilization and impedances consume the amount of power described.

Interface	Parameter	GV _{DD} (1.8 V)	GV _{DD} (2.5 V)	NV _{DD} (3.3 V)	LV _{DDA} / LV _{DDB} (3.3 V)	LV _{DDA} / LV _{DDB} (2.5 V)	LV _{DD} (3.3 V)	Unit	Comments
DDR 1, 60% utilization, 50% read/write	333 MHz, 32 bits	—	0.355	—	_	—	—	W	
$\begin{array}{l} R_{s} = 22 \ \Omega \\ R_{t} = 50 \ \Omega \\ \text{single pair of clock} \\ \text{capacitive load: data} = 8 \ pF, \\ \text{control address} = 8 \ pF, \\ \text{clock} = 8 \ pF \end{array}$	266 MHz, 32 bits	_	0.323	_	_	_	_	W	_
DDR 2, 60% utilization, 50% read/write	333 MHz, 32 bits	0.266	—	—		—	—	W	_
$\begin{array}{l} R_{s} = 22 \ \Omega \\ R_{t} = 75 \ \Omega \\ \text{single pair of clock} \\ \text{capacitive load: data} = 8 \ pF, \\ \text{control address} = 8 \ pF, \\ \text{clock} = 8 \ pF \end{array}$	266 MHz, 32 bits	0.246	_	_	_	_	_	W	_
PCI I/O load = 50 pF	33 MHz	—	_	0.120		—	—	W	_
	66 MHz		—	0.249		—	—	W	_
Local bus I/O load = 20 pF	66 MHz					—	0.056	W	_
	50 MHz	_	—	—	_	—	0.040	W	_
TSEC I/O load = 20 pF	MII, 25 MHz	—	_	—	0.008	_	—	W	Multiple by number of
	RGMII, 125 MHz	—	—	—	0.078	0.044	—	W	interface used

Table 5. MPC8313E Typical I/O Power Dissipation



5.2 **RESET AC Electrical Characteristics**

This table provides the reset initialization AC timing specifications.

Parameter/Condition	Min	Мах	Unit	Note
Required assertion time of HRESET or SRESET (input) to activate reset flow	32	_	t _{PCI_SYNC_IN}	1
Required assertion time of PORESET with stable clock and power applied to SYS_CLK_IN when the device is in PCI host mode	32		tsys_clk_in	2
Required assertion time of PORESET with stable clock and power applied to PCI_SYNC_IN when the device is in PCI agent mode	32	_	t _{PCI_SYNC_IN}	1
HRESET assertion (output)	512	_	t _{PCI_SYNC_IN}	1
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:3] and CFG_CLK_IN_DIV) with respect to negation of PORESET when the device is in PCI host mode	4	_	t _{SYS_CLK_IN}	2
Input setup time for POR configuration signals (CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV) with respect to negation of PORESET when the device is in PCI agent mode	4	_	^t PCI_SYNC_IN	1
Input hold time for POR configuration signals with respect to negation of HRESET	0	_	ns	_
Time for the device to turn off POR configuration signal drivers with respect to the assertion of $\overrightarrow{\text{HRESET}}$	_	4	ns	3
Time for the device to turn on POR configuration signal drivers with respect to the negation of $\overline{\text{HRESET}}$	1	-	t _{PCI_SYNC_IN}	1, 3

Notes:

1. t_{PCI_SYNC_IN} is the clock period of the input clock applied to PCI_SYNC_IN. When the device is In PCI host mode the

primary clock is applied to the SYS_CLK_IN input, and PCI_SYNC_IN period depends on the value of CFG_CLKIN_DIV. 2. t_{SYS_CLK_IN} is the clock period of the input clock applied to SYS_CLK_IN. It is only valid when the device is in PCI host mode.

POR configuration signals consists of CFG_RESET_SOURCE[0:2] and CFG_CLKIN_DIV.

This table provides the PLL lock times.

Table 11. PLL Lock Times

Parameter/Condition	Min	Мах	Unit	Note
PLL lock times	_	100	μs	

6 DDR and DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR SDRAM interface. Note that DDR SDRAM is $GV_{DD}(typ) = 2.5 \text{ V}$ and DDR2 SDRAM is $GV_{DD}(typ) = 1.8 \text{ V}$.



Table 36. eTSEC IEEE 1588 AC Timing Specifications (continued)

At recommended operating conditions with L/TV_{DD} of 3.3 V \pm 5%.

Parameter/Condition	Symbol	Min	Тур	Мах	Unit	Note
TSEC_1588_CLK peak-to-peak jitter	t _{T1588} CLKINJ	—	_	250	ps	
Rise time eTSEC_1588_CLK (20%-80%)	t _{T1588} CLKINR	1.0	_	2.0	ns	
Fall time eTSEC_1588_CLK (80%–20%)	t _{T1588} CLKINF	1.0	_	2.0	ns	
TSEC_1588_CLK_OUT clock period	t _{T1588} CLKOUT	$2 \times t_{T1588CLK}$	_	_	ns	
TSEC_1588_CLK_OUT duty cycle	^t t1588CLKOTH /t _{T1588} CLKOUT	30	50	70	%	
TSEC_1588_PULSE_OUT	t _{T1588OV}	0.5	_	3.0	ns	
TSEC_1588_TRIG_IN pulse width	t _{T1588} TRIGH	$2 \times t_{T1588CLK_MAX}$	_	—	ns	2

Notes:

1. T_{RX_CLK} is the max clock period of eTSEC receiving clock selected by TMR_CTRL[CKSEL]. See the *MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual,* for a description of TMR_CTRL registers.

2. It need to be at least two times of clock period of clock selected by TMR_CTRL[CKSEL]. See the MPC8313E PowerQUICC II Pro Integrated Processor Family Reference Manual, for a description of TMR_CTRL registers.

The maximum value of t_{T1588CLK} is not only defined by the value of T_{RX_CLK}, but also defined by the recovered clock. For example, for 10/100/1000 Mbps modes, the maximum value of t_{T1588CLK} is 3600, 280, and 56 ns, respectively.

8.5 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for MII, RMII, RGMII, SGMII, and RTBI are specified in Section 8.1, "Enhanced Three-Speed Ethernet Controller (eTSEC) (10/100/1000 Mbps)—MII/RMII/RGMII/SGMII/RTBI Electrical Characteristics."

8.5.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. Table 37 provide the DC electrical characteristics for MDIO and MDC.

Parameter	Symbol	Condi	Min	Мах	Unit	
Supply voltage (3.3 V)	NV _{DD}		2.97	3.63	V	
Output high voltage	V _{OH}	I _{OH} = -1.0 mA	NV _{DD} = Min	2.10	NV _{DD} + 0.3	V
Output low voltage	V _{OL}	$I_{OL} = 1.0 \text{ mA}$ $NV_{DD} = Min$		V _{SS}	0.50	V
Input high voltage	V _{IH}		2.0	_	V	
Input low voltage	V _{IL}		-		0.80	V
Input high current	I _{IH}	NV _{DD} = Max	$V_{IN}^{1} = 2.1 V$	—	40	μΑ
Input low current	Ι _{IL}	NV _{DD} = Max	V _{IN} = 0.5 V	-600	—	μΑ

 Table 37. MII Management DC Electrical Characteristics When Powered at 3.3 V



Table 37. MII Management DC Electrical Characteristics When Powered at 3.3 V (continued)

Note:

1. Note that the symbol V_{IN}, in this case, represents the NV_{IN} symbol referenced in Table 1 and Table 2.

8.5.2 MII Management AC Electrical Specifications

This table provides the MII management AC timing specifications.

Table 38. MII Management AC Timing Specifications

At recommended operating conditions with NV_{DD} is $3.3 \text{ V} \pm 0.3 \text{V}$

Parameter/Condition	Symbol ¹	Min	Тур	Мах	Unit	Note
MDC frequency	f _{MDC}	—	2.5	—	MHz	2
MDC period	t _{MDC}	—	400	—	ns	
MDC clock pulse width high	t _{MDCH}	32	—	—	ns	
MDC to MDIO delay	t _{MDKHDX}	10	—	170	ns	
MDIO to MDC setup time	t _{MDDVKH}	5	—	—	ns	
MDIO to MDC hold time	t _{MDDXKH}	0	—	—	ns	
MDC rise time	t _{MDCR}			10	ns	
MDC fall time	t _{MDHF}			10	ns	

Notes:

The symbols used for timing specifications follow the pattern of t<sub>(first two letters of functional block)(signal)(state)(reference)(state) for inputs and t_{(first two letters of functional block)(reference)(state)(signal)(state)} for outputs. For example, t_{MDKHDX} symbolizes management data timing (MD) for the time t_{MDC} from clock reference (K) high (H) until data outputs (D) are invalid (X) or data hold time. Also, t_{MDDVKH} symbolizes management data timing (MD) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{MDC} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
</sub>

2. This parameter is dependent on the csb_clk speed. (The MIIMCFG[Mgmt Clock Select] field determines the clock frequency of the Mgmt Clock EC_MDC.)

This figure shows the MII management AC timing diagram.



Figure 21. MII Management Interface Timing Diagram



9 High-Speed Serial Interfaces (HSSI)

This section describes the common portion of SerDes DC electrical specifications, which is the DC requirement for SerDes reference clocks. The SerDes data lane's transmitter and receiver reference circuits are also shown.

9.1 Signal Terms Definition

The SerDes utilizes differential signaling to transfer data across the serial link. This section defines terms used in the description and specification of differential signals.

Figure 22 shows how the signals are defined. For illustration purpose, only one SerDes lane is used for description. The figure shows waveform for either a transmitter output (TXn and \overline{TXn}) or a receiver input (RXn and \overline{RXn}). Each signal swings between A volts and B volts where A > B.

Using this waveform, the definitions are as follows. To simplify illustration, the following definitions assume that the SerDes transmitter and receiver operate in a fully symmetrical differential signaling environment.

1. Single-ended swing

The transmitter output signals and the receiver input signals TXn, \overline{TXn} , RXn, and \overline{RXn} each have a peak-to-peak swing of A – B volts. This is also referred as each signal wire's single-ended swing.

2. Differential output voltage, V_{OD} (or differential output swing):

The differential output voltage (or swing) of the transmitter, V_{OD} , is defined as the difference of the two complimentary output voltages: $V_{TXn} - V_{\overline{TXn}}$. The V_{OD} value can be either positive or negative.

3. Differential input voltage, V_{ID} (or differential input swing):

The differential input voltage (or swing) of the receiver, V_{ID} , is defined as the difference of the two complimentary input voltages: $V_{RXn} - V_{\overline{RXn}}$. The V_{ID} value can be either positive or negative.

- 4. Differential peak voltage, V_{DIFFp} The peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak voltage, $V_{DIFFp} = |A - B|$ volts.
- 5. Differential peak-to-peak, V_{DIFFp-p}

Since the differential output signal of the transmitter and the differential input signal of the receiver each range from A – B to –(A – B) volts, the peak-to-peak value of the differential transmitter output signal or the differential receiver input signal is defined as differential peak-to-peak voltage, $V_{DIFFp-p} = 2 \times V_{DIFFp} = 2 \times |(A - B)|$ volts, which is twice of differential swing in amplitude, or twice of the differential peak. For example, the output differential peak-peak voltage can also be calculated as $V_{TX-DIFFp-p} = 2 \times |V_{OD}|$.

6. Differential waveform

The differential waveform is constructed by subtracting the inverting signal (TX*n*, for example) from the non-inverting signal (TX*n*, for example) within a differential pair. There is only one signal trace curve in a differential waveform. The voltage represented in the differential waveform is not referenced to ground. Refer to Figure 22 as an example for differential waveform.

7. Common mode voltage, V_{cm}



of the differential pair must have a single-ended swing less than 800 mV and greater than 200 mV. This requirement is the same for both external DC-coupled or AC-coupled connection.

- For external DC-coupled connection, as described in Section 9.2.1, "SerDes Reference Clock Receiver Characteristics," the maximum average current requirements sets the requirement for average voltage (common mode voltage) to be between 100 and 400 mV. Figure 24 shows the SerDes reference clock input requirement for the DC-coupled connection scheme.
- For external AC-coupled connection, there is no common mode voltage requirement for the clock driver. Since the external AC-coupling capacitor blocks the DC level, the clock driver and the SerDes reference clock receiver operate in different command mode voltages. The SerDes reference clock receiver in this connection scheme has its common mode voltage set to $XCOREV_{SS}$. Each signal wire of the differential inputs is allowed to swing below and above the command mode voltage ($XCOREV_{SS}$). Figure 25 shows the SerDes reference clock input requirement for AC-coupled connection scheme.
- Single-ended mode
 - The reference clock can also be single-ended. The SD_REF_CLK input amplitude (single-ended swing) must be between 400 and 800 mV peak-to-peak (from V_{min} to V_{max}) with SD_REF_CLK either left unconnected or tied to ground.
 - The SD_REF_CLK input average voltage must be between 200 and 400 mV. Figure 26 shows the SerDes reference clock input requirement for the single-ended signaling mode.
 - To meet the input amplitude requirement, the reference clock inputs might need to be DC or AC coupled externally. For the best noise performance, the reference of the clock could be DC or AC coupled into the unused phase (SD_REF_CLK) through the same source impedance as the clock input (SD_REF_CLK) in use.



Figure 24. Differential Reference Clock Input DC Requirements (External DC-Coupled)





10.2 On-Chip USB PHY

This section describes the DC and AC electrical specifications for the on-chip USB PHY of the MPC8313E. See Chapter 7 in the USB Specifications Rev. 2, for more information.

This table provides the USB clock input (USB_CLK_IN) DC timing specifications.

Table 42. l	USB	CLK	IN DC	Electrical	Characteristics

Parameter	Symbol	Min	Мах	Unit
Input high voltage	V _{IH}	2.7	NV _{DD} + 0.3	V
Input low voltage	V _{IL}	-0.3	0.4	V

This table provides the USB clock input (USB_CLK_IN) AC timing specifications.

Table 43. USB_CLK	_IN AC Timing	J Specifications
-------------------	---------------	-------------------------

Parameter/Condition	Conditions	Symbol	Min	Тур	Мах	Unit
Frequency range	—	f _{USB_CLK_IN}	_	24	48	MHz
Clock frequency tolerance	_	^t CLK_TOL	-0.005	0	0.005	%
Reference clock duty cycle	Measured at 1.6 V	t _{CLK_DUTY}	40	50	60	%
Total input jitter/time interval error	Peak-to-peak value measured with a second order high-pass filter of 500 kHz bandwidth	t _{CLK_PJ}	—	_	200	ps



This table provides the DC electrical characteristics for the GPIO when the GPIO pins are operating from a 2.5-V supply.

Parameters	Symbol	Conditions		Min	Max	Unit
Supply voltage 2.5 V	NV _{DD}	—		2.37	2.63	V
Output high voltage	V _{OH}	I _{OH} = -1.0 mA	NV _{DD} = min	2.00	NV _{DD} + 0.3	V
Output low voltage	V _{OL}	I _{OL} = 1.0 mA	NV _{DD} = min	V _{SS} – 0.3	0.40	V
Input high voltage	V _{IH}	_	NV _{DD} = min	1.7	NV _{DD} + 0.3	V
Input low voltage	V _{IL}	_	NV _{DD} = min	-0.3	0.70	V
Input high current	Ι _{ΙΗ}	$V_{IN} = NV_{DD}$		—	10	μA
Input low current	۱ _{IL}	V _{IN} = V _{SS}		-15	—	μA

Table JU. OF TO TWITCH ODELATING AT 2.3 VI DO LIEUTIDAT CHATACTERISTICS

Note:

1. This specification only applies to GPIO pins that are operating from a 2.5-V supply. See Table 62 for the power supply listed for the individual GPIO signal

16.2 GPIO AC Timing Specifications

This table provides the GPIO input and output AC timing specifications.

Table 57. (GPIO Input	AC Timing	Specifications ¹
-------------	-------------------	------------------	-----------------------------

Characteristic	Symbol ²	Min	Unit
GPIO inputs—minimum pulse width	t _{PIWID}	20	ns

Notes:

1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLKIN. Timings are measured at the pin.

2. GPIO inputs and outputs are asynchronous to any visible clock. GPIO outputs should be synchronized before use by any external synchronous logic. GPIO inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation.

This figure provides the AC test load for the GPIO.



Figure 52. GPIO AC Test Load



This figure shows the SPI timing in slave mode (external clock).



Note: The clock edge is selectable on SPI.



This figure shows the SPI timing in master mode (internal clock).



Figure 55. SPI AC Timing in Master Mode (Internal Clock) Diagram

19 Package and Pin Listings

This section details package parameters, pin assignments, and dimensions. The MPC8313E is available in a thermally enhanced plastic ball grid array (TEPBGAII), see Section 19.1, "Package Parameters for the MPC8313E TEPBGAII," and Section 19.2, "Mechanical Dimensions of the MPC8313E TEPBGAII," for information on the TEPBGAII.

19.1 Package Parameters for the MPC8313E TEPBGAII

The package parameters are as provided in the following list. The package type is 27 mm \times 27 mm, 516 TEPBGAII.

Package outline	$27 \text{ mm} \times 27 \text{ mm}$
Interconnects	516
Pitch	1.00 mm
Module height (typical)	2.25 mm
Solder Balls	96.5 Sn/3.5 Ag(VR package),
	62 Sn/36 Pb/2 Ag (ZQ package) Ball diameter (typical)
0.6 mm	



19.2 Mechanical Dimensions of the MPC8313E TEPBGAII

This figure shows the mechanical dimensions and bottom surface nomenclature of the 516-TEPBGAII package.



Notes:

- 1. All dimensions are in millimeters.
- 2. Dimensions and tolerances per ASME Y14.5M-1994.
- 3. Maximum solder ball diameter measured parallel to datum A.
- 4. Datum A, the seating plane, is determined by the spherical crowns of the solder balls.
- 5. Package code 5368 is to account for PGE and the built-in heat spreader.

Figure 56. Mechanical Dimension and Bottom Surface Nomenclature of the MPC8313E TEPBGAII



Signal Package Pin Number		Pin Type	Power Supply	Note
LA24	E23	0	LV _{DD}	11
LA25	D22	0	LV _{DD}	11
LCS0	D23	0	LV _{DD}	10
LCS1	J26	0	LV _{DD}	10
LCS2	F22	0	LV _{DD}	10
LCS3	D26	0	LV _{DD}	10
LWE0/LFWE	E24	0	LV _{DD}	10
LWE1	H26	0	LV _{DD}	10
LBCTL	L22	0	LV _{DD}	10
LALE/M1LALE/M2LALE	E26	0	LV _{DD}	11
LGPL0/LFCLE	AA23	0	LV _{DD}	_
LGPL1/LFALE	AA24	0	LV _{DD}	_
LGPL2/LOE/LFRE	AA25	0	LV _{DD}	10
LGPL3/LFWP	AA26 O		LV _{DD}	_
LGPL4/LGTA/LUPWAIT/LFRB	Y22 I/O		LV _{DD}	2
LGPL5	E21	0	LV _{DD}	10
LCLK0	H22	0	LV _{DD}	11
LCLK1	G26	G26 O		11
LA0/GPIO0/MSRCID0	AC24	I/O	LV _{DD}	_
LA1/GPIO1//MSRCID1	Y24	I/O	LV _{DD}	_
LA2/GPIO2//MSRCID2	Y26	I/O	LV _{DD}	_
LA3/GPIO3//MSRCID3	W22	I/O	LV _{DD}	_
LA4/GPIO4//MSRCID4	W24	I/O	LV _{DD}	_
LA5/GPIO5/MDVAL	W26	I/O	LV _{DD}	_
LA6/GPIO6	V22	V22 I/O		_
LA7/GPIO7/TSEC_1588_TRIG2	V23	I/O	LV _{DD}	8
LA8/GPIO13/TSEC_1588_ALARM1	V24	I/O	LV _{DD}	8
LA9/GPIO14/TSEC_1588_PP3	V25 I/O		LV _{DD}	8
LA10/TSEC_1588_CLK	V26	0	LV _{DD}	8
LA11/TSEC_1588_GCLK	U22	0	LV _{DD}	8
LA12/TSEC_1588_PP1	AD24	0	LV _{DD}	8
LA13/TSEC_1588_PP2	L25	0	LV _{DD}	8

Table 62. MPC8313E TEPBGAII Pinout Listing (continued)



Table 62. MPC8313E TEPBGAII Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Note		
LA14/TSEC_1588_TRIG1	L24	0	LV _{DD}	8		
LA15/TSEC_1588_ALARM2	K26	0	LV _{DD}	8		
	DUART		·			
UART_SOUT1/MSRCID0	N2	0	NV _{DD}	—		
UART_SIN1/MSRCID1	M5	I/O	NV _{DD}	—		
UART_CTS1/GPIO8/MSRCID2	M1	I/O	NV _{DD}	—		
UART_RTS1/GPIO9/MSRCID3	K1	I/O	NV _{DD}	—		
UART_SOUT2/MSRCID4/TSEC_1588_CLK	M3	0	NV _{DD}	8		
UART_SIN2/MDVAL/TSEC_1588_GCLK	L1	I/O	NV _{DD}	8		
UART_CTS2/TSEC_1588_PP1	L5	I/O	NV _{DD}	8		
UART_RTS2/TSEC_1588_PP2	L3	I/O	NV _{DD}	8		
ľ	² C interface		·			
IIC1_SDA/CKSTOP_OUT/TSEC_1588_TRIG1	J4	I/O	NV _{DD}	2, 8		
IIC1_SCL/CKSTOP_IN/TSEC_1588_ALARM2	J2	I/O	NV _{DD}	2, 8		
IIC2_SDA/PMC_PWR_OK/GPIO10	J3	I/O	NV _{DD}	2		
IIC2_SCL/GPIO11	H5	I/O	NV _{DD}	2		
	Interrupts					
MCP_OUT	G5	0	NV _{DD}	2		
IRQ0/MCP_IN	K5	I	NV _{DD}	—		
IRQ1	K4	I	NV _{DD}	—		
IRQ2	K2	I	NV _{DD}	—		
IRQ3/CKSTOP_OUT	К3	I/O	NV _{DD}	—		
IRQ4/CKSTOP_IN/GPIO12	J1	I/O	NV _{DD}	—		
Configuration						
CFG_CLKIN_DIV	D5	I	NV _{DD}	—		
EXT_PWR_CTRL	J5	0	NV _{DD}	—		
CFG_LBIU_MUX_EN	R24	I	NV _{DD}	—		
	JTAG					
ТСК	E1	I	NV _{DD}	_		
TDI	E2	I	NV _{DD}	4		
TDO	E3	0	NV _{DD}	3		



RCWL[SPMF]	System PLL Multiplication Factor
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

Table 65. System PLL Multiplication Factors (continued)

Note:

1. If RCWL[DDRCM] and RCWL[LBCM] are both cleared, the system PLL VCO frequency = (CSB frequency) × (System PLL VCO Divider).

2. If either RCWL[DDRCM] or RCWL[LBCM] are set, the system PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO Divider).

3. The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz

As described in Section 20, "Clocking," the LBCM, DDRCM, and SPMF parameters in the reset configuration word low and the CFG_CLKIN_DIV configuration input signal select the ratio between the primary clock input (SYS_CLK_IN or PCI_SYNC_IN) and the internal coherent system bus clock (*csb_clk*). This table shows the expected frequency values for the CSB frequency for select *csb_clk* to SYS_CLK_IN/PCI_SYNC_IN ratios.

			Inp	out Clock Fre	equency (MH	lz) ²
CFG_CLKIN_DIV at Reset ¹	SPMF	<i>csb_clk</i> :Input Clock Ratio ²	24	25	33.33	66.67
			csb_clk Frequency (MHz))
High	0010	2:1				133
High	0011	3:1			100	
High	0100	4:1		100	133	
High	0101	5:1	120	125	167	
High	0110	6:1	144	150		
Low	0010	2:1				133
Low	0011	3:1			100	
Low	0100	4:11		100	133	
Low	0101	5:1	120	125	167	
Low	0110	6:1	144	150		

Table 66. CSB Frequency Options

¹ CFG_CLKIN_DIV select the ratio between SYS_CLK_IN and PCI_SYNC_OUT.

² SYS_CLK_IN is the input clock in host mode; PCI_CLK is the input clock in agent mode.



• Third, between the device and any SerDes voltage regulator there should be a $10-\mu$ F, low equivalent series resistance (ESR) SMT tantalum chip capacitor and a $100-\mu$ F, low ESR SMT tantalum chip capacitor. This should be done for all SerDes supplies.

22.5 Connection Recommendations

To ensure reliable operation, it is highly recommended to connect unused inputs to an appropriate signal level. Unused active low inputs should be tied to NV_{DD} , GV_{DD} , LV_{DD} , LV_{DDA} , or LV_{DDB} as required. Unused active high inputs should be connected to V_{SS} . All NC (no-connect) signals must remain unconnected.

Power and ground connections must be made to all external V_{DD} , NV_{DD} , GV_{DD} , LV_{DD} , LV_{DDA} , LV_{DDB} , and V_{SS} pins of the device.

22.6 Output Buffer DC Impedance

The MPC8313E drivers are characterized over process, voltage, and temperature. For all buses, the driver is a push-pull single-ended driver type (open drain for I^2C).

To measure Z_0 for the single-ended drivers, an external resistor is connected from the chip pad to NV_{DD} or V_{SS} . Then, the value of each resistor is varied until the pad voltage is $NV_{DD}/2$ (see Figure 60). The output impedance is the average of two components, the resistances of the pull-up and pull-down devices. When data is held high, SW1 is closed (SW2 is open), and R_p is trimmed until the voltage at the pad equals $NV_{DD}/2$. R_p then becomes the resistance of the pull-up devices. R_p and R_N are designed to be close to each other in value. Then, $Z_0 = (R_p + R_N)/2$.



Figure 60. Driver Impedance Measurement

The value of this resistance and the strength of the driver's current source can be found by making two measurements. First, the output voltage is measured while driving logic 1 without an external differential termination resistor. The measured voltage is $V_1 = R_{source} \times I_{source}$. Second, the output voltage is measured while driving logic 1 with an external precision differential termination resistor of value R_{term} . The measured voltage is $V_2 = (1/(1/R_1 + 1/R_2)) \times I_{source}$. Solving for the output impedance gives $R_{source} = R_{term} \times (V_1/V_2 - 1)$. The drive current is then $I_{source} = V_1/R_{source}$.



Table 73	. Document	Revision	History	(continued)
----------	------------	----------	---------	-------------

Rev. Number	Date	Substantive Change(s)
1	3/2008	 In Table 63, added LBC_PM_REF_10 & LSRCID3 as muxed with USBDR_PCTL1 In Table 63, added LSRCID2 as muxed with USBDR_PCTL0 In Table 63, added LSRCID0 as muxed with USBDR_PWRFAULT In Table 63, added LSRCID0 as muxed with USBDR_DRIVE_VBUS In Table 63, moved T1, U2,& V2 from V_{DD} to XCOREVDD. In Table 63, moved P2, R2, & T3 from V_{SS} to XCOREVSS. In Table 63, moved P3, & V4 from V_{DD} to XPADVDD. In Table 63, neved "Double with pad" for AV_{DD1} and AV_{DD2} and moved AV_{DD1} and AV_{DD2} to Power and Ground Supplies section In Table 63, added muxing in pinout to show new options for selecting IEEE 1588 functionality. Added footnote 8 In Table 63, updated muxing in pinout to show new LBC ECC boot enable control muxed with eTSEC1_MDC Added pin type information for power supplies. Removed N1 and N3 from Vss section of Table 63. Added Therm0 and Therm1 (N1 and N3, respectively). Added note 7 to state: "Internal thermally sensitive resistor value varies linearly with temperature. Useful for determining the junction temperature." In Table 65 corrected maximum frequency of Local Bus Frequency from "33–66" to 66 MHz In Table 65 corrected maximum frequency of PCI from "24–66" to 66 MHz Added "which is determined by RCWLR[COREPLL]," to the note in Section 20.2, "Core PLL Configuration" about the VCO divider.
0	6/2007	 Added "(VCOD)" next to VCO divider column in Table 68. Added footnote stating that core_clk frequency must not exceed its maximum, so 2.5:1 and 3:1 <i>core_clk:csb_clk</i> ratios are invalid for certain <i>csb_clk</i> values. In Table 69, notes were confusing. Added note 3 for VCO column, note 4 for CSB (<i>csb_clk</i>) column, note 5 for USB ref column, and note 6 to replace "Note 1". Clarified note 4 to explain erratum eTSEC40. In Table 69, updated note 6 to specify USB reference clock frequencies limited to 24 and 48 for rev. 2 silicon. Replaced Table 71 "Thermal Resistance for TEPBGAII with Heat Sink in Open Flow". Removed last row of Table 19. Removed last row of Table 19. Removed 200 MHz rows from Table 21 and Table 5. Changed VIH minimum spec from 2.0 to 2.1 for clock, PIC, JTAG, SPI, and reset pins in Table 9, Table 47, Table 54, Table 59, and Table 61. Added Figure 4 showing the DDR input timing diagram. In Table 19, removed "MDM" from the "MDQS-MDQ/MECC/MDM" text under the Parameter column for the tCISKEW parameter. MDM is an output signal and should be removed from the input AC timing spec table (tCISKEW). Added "and power" to rows 2 and 3 in Table 10 Added the sentence "Once both the power supplies" and PORESET to Section 2.2, "Power Sequencing," and Figure 3. In Figure 35, corrected "USB0_CLK/USB1_CLK/DR_CLK" with "USBDR_CLK" In Table 42, clarified that AC specs are for ULPI only.
0	6/2007	Initial release.

How to Reach Us:

Home Page: www.freescale.com

Web Support: http://www.freescale.com/support

USA/Europe or Locations Not Listed:

Freescale Semiconductor, Inc. Technical Information Center, EL516 2100 East Elliot Road Tempe, Arizona 85284 1-800-521-6274 or +1-480-768-2130 www.freescale.com/support

Europe, Middle East, and Africa:

Freescale Halbleiter Deutschland GmbH Technical Information Center Schatzbogen 7 81829 Muenchen, Germany +44 1296 380 456 (English) +46 8 52200080 (English) +49 89 92103 559 (German) +33 1 69 35 48 48 (French) www.freescale.com/support

Japan:

Freescale Semiconductor Japan Ltd. Headquarters ARCO Tower 15F 1-8-1, Shimo-Meguro, Meguro-ku Tokyo 153-0064 Japan 0120 191014 or +81 3 5437 9125 support.japan@freescale.com

Asia/Pacific:

Freescale Semiconductor China Ltd. Exchange Building 23F No. 118 Jianguo Road Chaoyang District Beijing 100022 China +86 10 5879 8000 support.asia@freescale.com

For Literature Requests Only:

Freescale Semiconductor Literature Distribution Center P.O. Box 5405 Denver, Colorado 80217 1-800 441-2447 or +1-303-675-2140 Fax: +1-303-675-2150 LDCForFreescaleSemiconductor @hibbertgroup.com

Document Number: MPC8313EEC Rev. 4 11/2011 Information in this document is provided solely to enable system and software implementers to use Freescale Semiconductor products. There are no express or implied copyright licenses granted hereunder to design or fabricate any integrated circuits or integrated circuits based on the information in this document.

Freescale Semiconductor reserves the right to make changes without further notice to any products herein. Freescale Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Freescale Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Freescale Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Freescale Semiconductor does not convey any license under its patent rights nor the rights of others. Freescale Semiconductor products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Freescale Semiconductor product could create a situation where personal injury or death may occur. Should Buyer purchase or use Freescale Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold Freescale Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Freescale Semiconductor was negligent regarding the design or manufacture of the part.

Freescale and the Freescale logo are trademarks of Freescale Semiconductor, Inc. Reg. U.S. Pat. & Tm. Off. QorlQ is a trademark of Freescale Semiconductor, Inc. All other product or service names are the property of their respective owners. The Power Architecture and Power.org word marks and the Power and Power.org logos and related marks are trademarks and service marks licensed by Power.org. RapidIO is a registered trademark of the RapidIO Trade Association. IEEE 1588 and 1149.1 are registered trademarks of the Institute of Electrical and Electronics Engineers, Inc. (IEEE). This product is not endorsed or approved by the IEEE.

© 2007–2011 Freescale Semiconductor, Inc.



